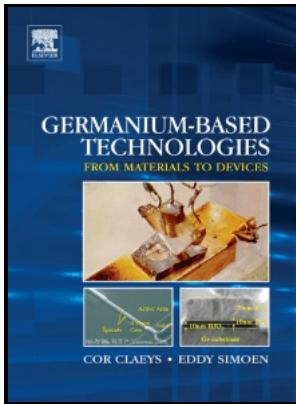


Ion implantation range data for silicon and germanium device technologies

Learned Information (Europe) Ltd. - Ion implantation as an enabling technique for the fabrication of back



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The layer 84 is located at a preselected depth position of the N- type collector layer 76.

Ion implantation in silicon to facilitate testing of photonic circuits

The polycrystalline silicon layer 22 acts as the gate electrode of the MOSFET 10, while the underlying thermal oxide thin-film 18 functions as a gate insulation layer. Communication device for a logic circuit 1998-02-13 2003-09-30 Micron Technology, Inc.

ION IMPLANTATION OF SILICON AND GERMANIUM AT ROOM TEMPERATURE. ANALYSIS BY MEANS OF 1.0

The crystal orientation of the layer can be engineered to match that of the target, even though the exact crystal structure and lattice constant may be very different. The source is closely coupled to biased electrodes for extraction of the ions into the beamline and most often to some means of selecting a particular ion species for transport into the main accelerator section.

Ion implantation in silicon to facilitate testing of photonic circuits

This modifies the conductivity of the semiconductor in its vicinity. The germanium-ion implantation technique for forming the heterostructure inside the silicon substrate can be applied to bipolar transistor devices. Finally, the implanted surface is coupled with some method for collecting the accumulated charge of the implanted ions so that the delivered dose can be measured in a continuous fashion and the implant process stopped at the desired dose level.

Ion Implantation

Ion implantation as an enabling technique for the fabrication of back

The structural change caused by the implantation produces a surface compression in the steel, which prevents crack propagation and thus makes the material more resistant to fracture. Depending on the value of x , the band gap of the films changes from 1.

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